

L Number	Hits	Search Text	DB	Time stamp
1	4	single adj cmos adj pair	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/07 09:32
-	246	cmos adj pair	USPAT; US-PGPUB	2003/05/06 09:45
-	293	cmos adj pair	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/05 15:45
-	103	(cmos adj pair) and (257/\$.ccls. or 438/\$.ccls.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/05 16:05
-	62	(third adj mosfet) same threshold	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/05 16:05
-	12	(cmos adj pair) and ((oxide or insulator) adj oxides)	USPAT; US-PGPUB	2003/05/06 09:48
-	0	(cmos adj pair) and ((oxide or insulator) adj oxide adj thickness)	USPAT; US-PGPUB	2003/05/06 09:48
-	28	(cmos adj pair) and ((oxide or insulator) adj thickness)	USPAT; US-PGPUB	2003/05/06 09:59
-	28	(cmos adj pair) and ((oxide or insulator) adj thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:00
-	31	(multiple adj (oxide or insulator) adj thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:05
-	46	(multiple adj gate adj (oxide or insulator) adj thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:17
-	0	6037222.pn. and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/06 10:18
-	1	6258673.pn. and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/07 09:31